Guoxing Duan

List of Publications by Year
in descending order

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6 papers	136 citations	6 h-index (1478505)	6 g-index (1872680)
6 all docs	6 docs citations	6 times ranked	229 citing authors

#	Article	IF	Citations
1	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe ${p}$ MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	2.0	16
2	Total Ionizing Dose Effects on Ge Channel <formula formulatype="inline"><tex Notation="TeX">p</tex></formula>FETs with Raised <formula formulatype="inline"><tex Notation="TeX">${m Si}_{0.55}{m Ge}_{0.45}$</tex></formula> Source/Drain. IEEE Transactions on Nuclear Science, 2015, 62, 2412-2416.	2.0	7
3	Activation Energies for Oxide- and Interface-Trap Charge Generation Due to Negative-Bias Temperature Stress of Si-Capped SiGe-pMOSFETs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 352-358.	2.0	9
4	Electrical Stress and Total Ionizing Dose Effects on <formula formulatype="inline"><tex Notation="TeX">${hbox {MoS}}_{2}$</tex> </formula> Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 2862-2867.	2.0	20
5	Total Ionizing Dose Effects on hBN Encapsulated Graphene Devices. IEEE Transactions on Nuclear Science, 2014, 61, 2868-2873.	2.0	27
6	Bias Dependence of Total Ionizing Dose Effects in SiGe-MOS FinFETs<formula formulatype="inline"> <tex Notation="TeX"/> </formula>. IEEE Transactions on Nuclear Science, 2014, 61, 2834-2838.	2.0	57